

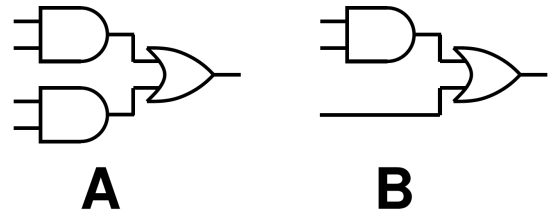
ESE535: Electronic Design Automation

Day 23: April 10, 2013
Statistical Static Timing Analysis



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Delay PDFs? (2a)

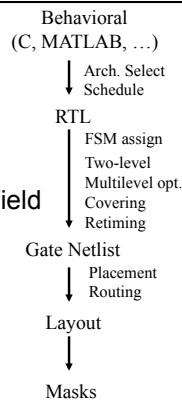


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Today

- Sources of Variation
- Limits of Worst Case
- Optimization for Parametric Yield
- Statistical Analysis

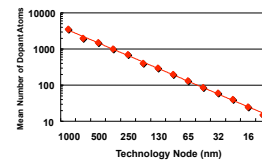


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Central Problem

- As our devices approach the atomic scale, we must deal with statistical effects governing the placement and behavior of individual atoms and electrons.

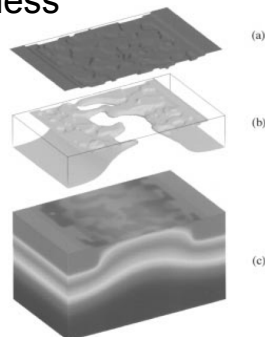


- Transistor critical dimensions
- Atomic discreteness
- Subwavelength litho
- Etch/polish rates
- Focus
- Number of dopants
- Dopant Placement

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Oxide Thickness



[Asenov et al. TRED 2002]

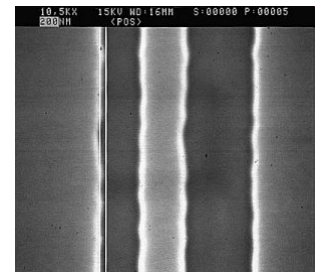
Fig. 1. (a) Typical profile of the random Si/SiO₂ interface in a 10 × 10 nm² MOSFET, followed by (b) an equipotential contour obtained from DG simulations, and (c) the potential distribution.

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Line Edge Roughness

- 1.2μm and 2.4μm lines



From:
http://www.microtechweb.com/2d/lw_pict.htm

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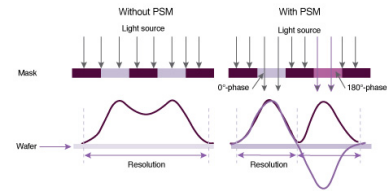
Light

- What is wavelength of visible light?

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Phase Shift Masking



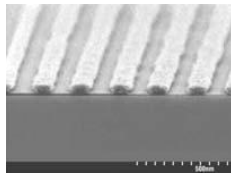
Source

<http://www.synopsys.com/Tools/Manufacturing/MaskSynthesis/PSMCreate/Pages/default.aspx>

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Line Edges (PSM)



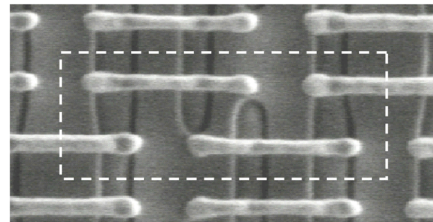
Source:

http://www.solid-state.com/display_article/122066/5/none/none/Feat/Developments-in-materials-for-157nm-photoresists

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Intel 65nm SRAM (PSM)



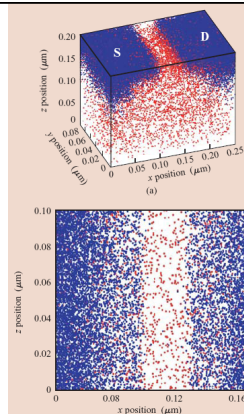
Source:

http://www.intel.com/technology/itj/2008/v12i2/5-design/figures/Figure_5_lg.gif

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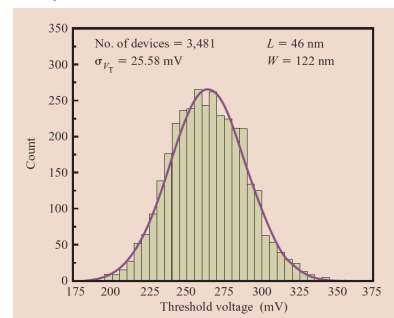
Statistical Dopant Placement



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[Bernstein et al, IBM JRD 2006]

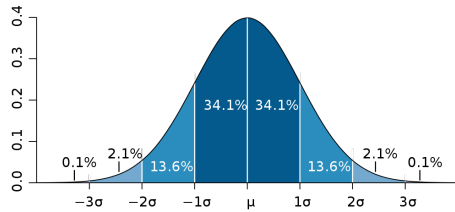
V_{th} Variability @ 65nm



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[Bernstein et al, IBM JRD 2006]

Gaussian Distribution



From: http://en.wikipedia.org/wiki/File:Standard_deviation_diagram.svg

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ITRS 2005 Variation (3σ)

Table 18a Design-for-Manufacturability—Near-term Years

Year of Production	2005	2006	2007	2008	2009	2010	2011	2012	2013	Driver
DRAM % Pitch (nm) (contracted)	80	70	65	57	50	45	40	36	32	
Mask cost (\$m) from publicly available data	1.5	2.2	3.0	4.5	6.0	9.0	12.0	18.0	24.0	SOC
% V_{th} Variability	10%	10%	10%	10%	10%	10%	10%	10%	10%	SOC

Table 18b Design-for-Manufacturability—Long-term Years

Year of Production	2014	2015	2016	2017	2018	2019	2020	Driver
DRAM % Pitch (nm)(contracted)	28	25	22	20	18	16	14	
Mask cost (\$m) from publicly available data	36.0	48.0	72.0	96.0	144.0	192.0	288.0	SOC
% V_{th} Variability	10%	10%	10%	10%	10%	10%	10%	SOC
% V_{th} variability seen at on-chip circuits	10%	10%	10%	10%	10%	10%	10%	SOC
% V_{th} variability	81%	81%	81%	81%	112%	112%	112%	SOC
Doping Variability impact on VTH								SOC
% V_{th} variability Includes all sources	81%	81%	81%	81%	112%	112%	112%	SOC
% CD variability CD for now, might add doping later	10%	10%	10%	10%	10%	10%	10%	SOC
% circuit performance variability circuit compensating gates and vires	58%	61%	62%	65%	66%	69%	69%	SOC
% circuit power variability circuit compensating gates and vires	59%	60%	60%	61%	61%	62%	62%	SOC

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Example: V_{th}

- Many physical effects impact V_{th}
 - Doping, dimensions, roughness
- Behavior highly dependent on V_{th}

$$I_{DS} = \frac{\mu_n C_{OX}}{2} \left(\frac{W}{L} \right) \left[(V_{GS} - V_T)^2 \right]$$

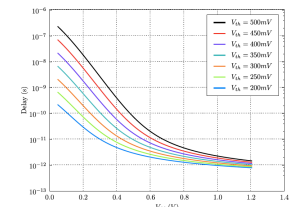
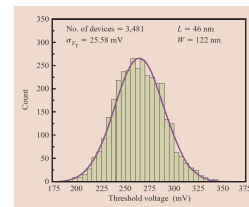
$$I_{DS} = I_S \left(\frac{W}{L} \right) e^{\left(\frac{V_{GS}}{n k T / q} \right)} \left(1 - e^{-\left(\frac{V_{DS}}{k T / q} \right)} \right) (1 + \lambda V_{DS})$$

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Impact Performance

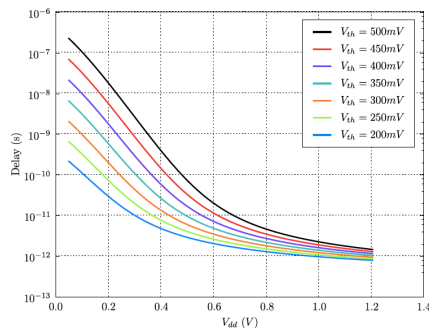
- $V_{th} \rightarrow I_{ds} \rightarrow \text{Delay} (R_{on} * C_{load})$



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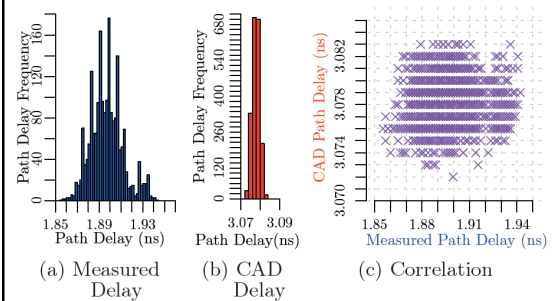
Impact of V_{th} Variation



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Variation in Current FPGAs

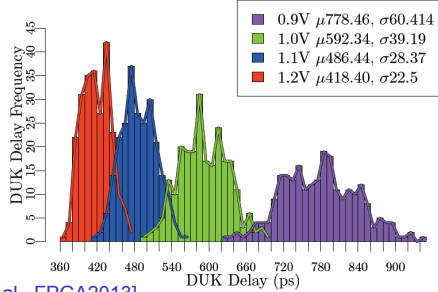


[Gojman et al., FPGA2013]

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Reduce Vdd (Cyclone IV 60nm LP)



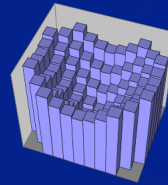
[Gojman et al., FPGA2013]

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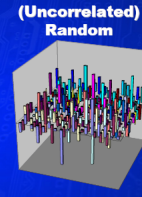
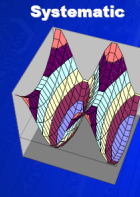
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Scale of Variations

Die-to-Die (D2D)
Variations



Within-Die (WID)
Variations

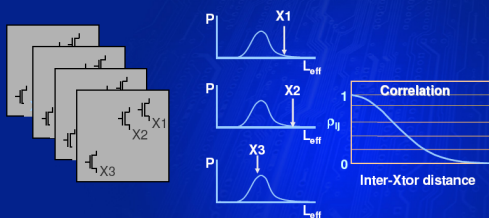


Source: Noel Menezes, Intel ISPD2007

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Nature of correlated variation



- CDs of transistors that are close track
- Tracking diminishes with distance

Source: Noel Menezes, Intel ISPD2007

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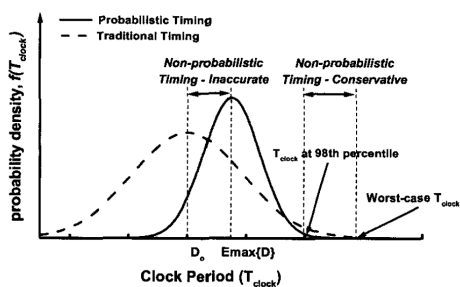
Old Way

- Characterize gates by corner cases
 - Fast, nominal, slow
- Add up corners to estimate range
- Preclass:
 - Slow corner: 1.1
 - Nominal: 1.0
 - Fast corner: 0.9

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Corners Misleading

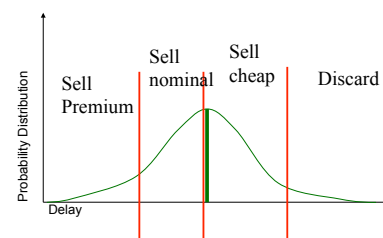


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[Orshansky+Keutzer DAC 2002]

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Parameteric Yield

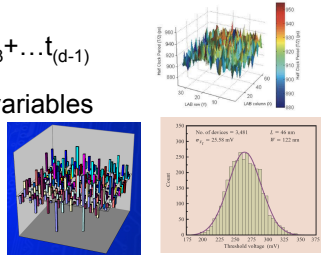


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Phenomena 1: Path Averaging

- $T_{\text{path}} = t_0 + t_1 + t_2 + t_3 + \dots + t_{(d-1)}$
- T_i – iid random variables
 - Mean τ
 - Variance σ
- T_{path}
 - Mean $d \times \tau$
 - Variance $= \sqrt{d} \times \sigma$



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Sequential Paths

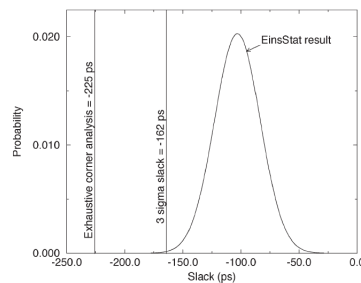
- $T_{\text{path}} = t_0 + t_1 + t_2 + t_3 + \dots + t_{(d-1)}$
- T_{path}
 - Mean $d \times \tau$
 - Variance $= \sqrt{d} \times \sigma$
- 3 sigma delay on path: $d \times \tau + 3\sqrt{d} \times \sigma$
 - Worst case per component would be: $d \times (\tau + 3 \sigma)$
 - **Overestimate d vs. $\sqrt{d}$**

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SSTA vs. Corner Models

- STA with corners predicts 225ps
- SSTA predicts 162ps at 3σ
- **SSTA reduces pessimism by 28%**



[Slide composed by Nikil Mehta]

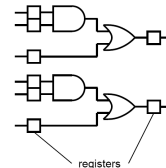
Fig. 11. EinsStat result on industrial ASIC design for early mode slacks.

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Source: IBM, TRCAD 2006²⁷

Phenomena 2: Parallel Paths

- Cycle time limited by slowest path
- $T_{\text{cycle}} = \max(T_{p0}, T_{p1}, T_{p2}, \dots, T_{p(n-1)})$
- $P(T_{\text{cycle}} < T_0) = P(T_{p0} < T_0) \times P(T_{p1} < T_0) \dots$
- $= [P(T_p < T_0)]^n$
- $0.5 = [P(T_p < T_{50})]^n$
- $P(T_p < T_{50}) = (0.5)^{(1/n)}$

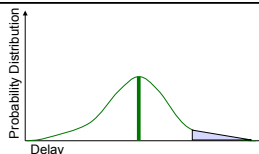


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System Delay

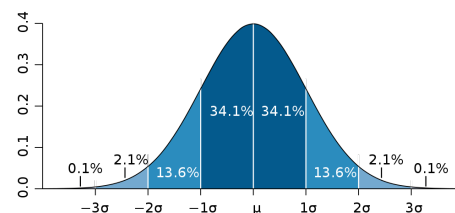
- $P(T_p < T_{50}) = (0.5)^{(1/n)}$
 - $N=10^8 \rightarrow 0.999999993$
 - 1.7×10^{-9}
 - $N=10^{10} \rightarrow 0.99999999993$
 - 1.7×10^{-11}



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Gaussian Distribution



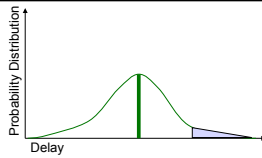
From: http://en.wikipedia.org/wiki/File:Standard_deviation_diagram.svg

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System Delay

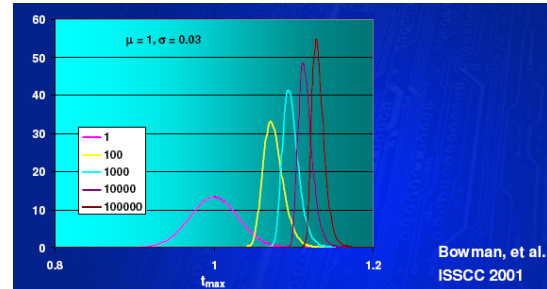
- $P(T_p < T_{50}) = (0.5)^{(1/n)}$
 - $N=10^8 \rightarrow 0.999999993$
 - $1-7 \times 10^{-9}$
 - $N=10^{10} \rightarrow 0.99999999993$
 - $1-7 \times 10^{-11}$
- For 50% yield want
 - 6 to 7 σ
 - $T_{50} = T_{\text{mean}} + 7\sigma_{\text{path}}$



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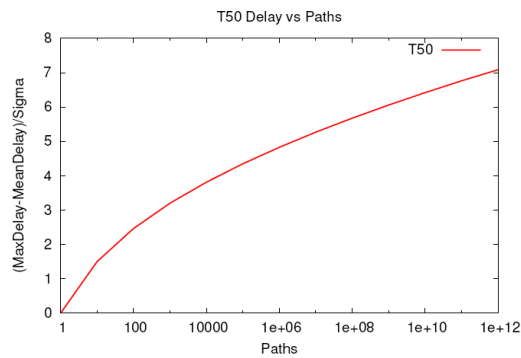
System Delay



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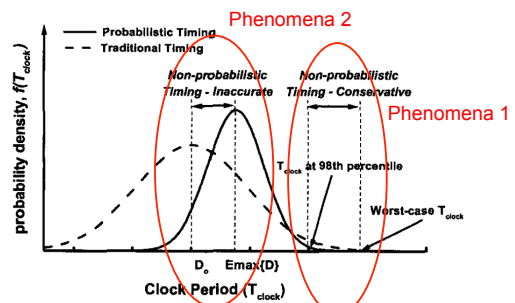
System Delay



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Corners Misleading

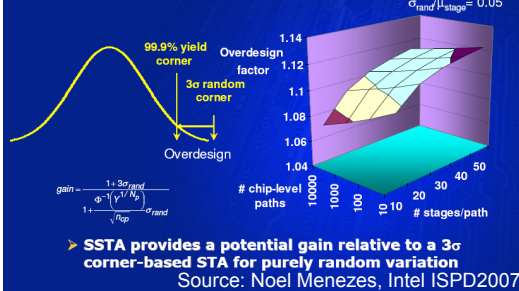


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[Orshansky+Keutzer DAC 2002]

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SSTA gain relative to 3 σ corner analysis: Random

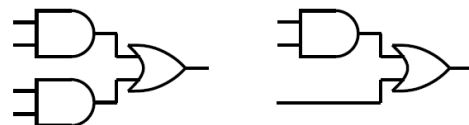


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But does worst-case mislead?

- STA with worst-case says these are equivalent:

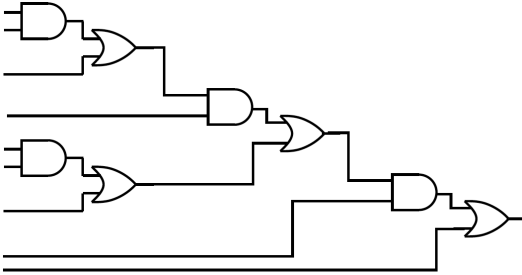


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But does worst-case mislead?

- STA Worst case delay for this?

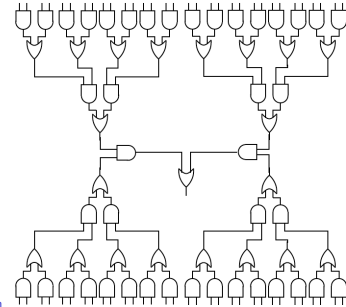


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But does worst-case mislead?

- STA Worst case delay for this?

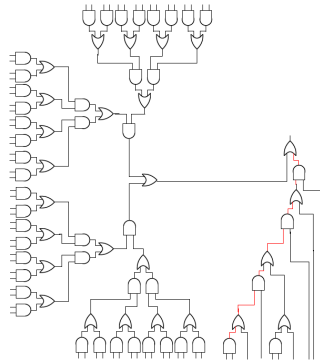


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Does Worst-Case Mislead?

- Delay of off-critical path may matter
- Best case delay of critical path?
- Worst-case delay of non-critical path?



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What do we need to do?

- Ideal:
 - Compute PDF for delay at each gate
 - Compute delay of a gate as a PDF from:
 - PDF of inputs
 - PDF of gate delay

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Delay Calculation

Day 22

AND rules

$i_1 \rightarrow$ $i_2 \downarrow$	0	1	2
0	0 $MIN(l_1, l_2) + d$ $MIN(u_1, u_2) + d$	0 $l_2 + d$ $u_2 + d$	0 $MIN(l_1, l_2) + d$ $u_2 + d$
1	0 $l_1 + d$ $u_1 + d$	1 $MAX(l_1, l_2) + d$ $MAX(u_1, u_2) + d$	2 $l_1 + d$ $MAX(u_1, u_2) + d$
2	0 $MIN(l_1, l_2) + d$ $u_1 + d$	2 $l_2 + d$ $MAX(u_1, u_2) + d$	2 $MIN(l_1, l_2) + d$ $MAX(u_1, u_2) + d$

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What do we need to do?

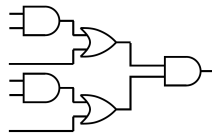
- Ideal:
 - compute PDF for delay at each gate
 - Compute delay of a gate as a PDF from:
 - PDF of inputs
 - PDF of gate delay
 - Need to compute for distributions
 - SUM
 - MAX (maybe MIN)

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For Example

- Consider entry:
– $\text{MAX}(u_1, u_2) + d$



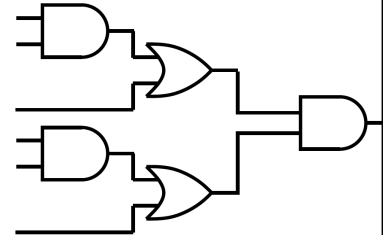
$i_1 \rightarrow$ $i_2 \downarrow$	0	1	2
0	$\text{MIN}(l_1, l_2) + d$ $\text{MIN}(u_1, u_2) + d$	$l_2 + d$ $u_2 + d$	$\text{MIN}(l_1, l_2) + d$ $u_2 + d$
1	$l_1 + d$ $u_1 + d$	$\text{MAX}(l_1, l_2) + d$ $\text{MAX}(u_1, u_2) + d$	$l_1 + d$ $\text{MAX}(u_1, u_2) + d$
2	$\text{MIN}(l_1, l_2) + d$ $u_1 + d$	$l_2 + d$ $\text{MAX}(u_1, u_2) + d$	$\text{MIN}(l_1, l_2) + d$ $\text{MAX}(u_1, u_2) + d$

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MAX

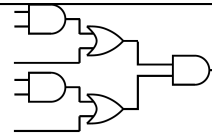
- Compute MAX of two input distributions.



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SUM

- Add that distribution to gate distribution.



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Continuous

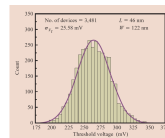
- Can roughly carry through PDF calculations with Gaussian distributions rather than discrete PDFs

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Dealing with PDFs

- Simple model assume all PDFs are Gaussian
 - Model with mean, σ
 - Imperfect
 - Not all phenomena are Gaussian
 - Sum of Gaussians is Gaussian
 - Max of Gaussians is **not** a Gaussian

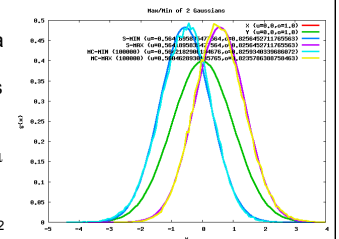


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MAX of Two Identical Gaussians

- Max of Gaussians is not a Gaussian
- Can try to approximate as Gaussian
- Given two identical Gaussians A and B with μ and σ
- Plug into equations
- $E[\text{MAX}(A, B)] = \mu + \sigma/(\pi)^{1/2}$
- $\text{VAR}[\text{MAX}(A, B)] = \sigma^2 - \sigma/\pi$
- [Source: Nikil Mehta]



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Probability of Path Being Critical

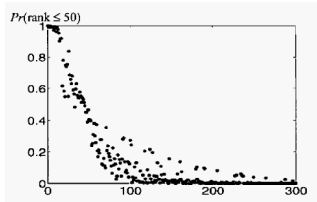
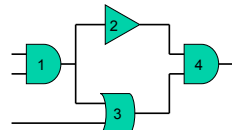
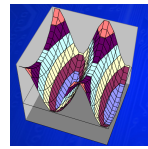
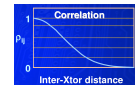


Figure 1 Probability that a path shows up in top 50 paths (Data from Monte Carlo simulation of a 90nm microprocessor block)

[Source: Intel DAC 2005]

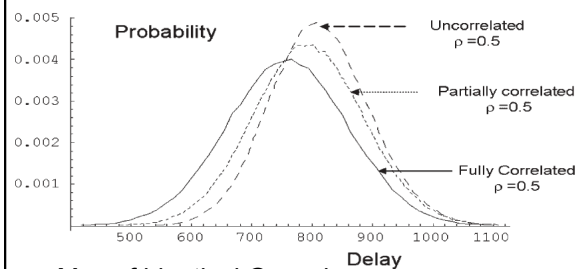
More Technicalities

- Correlation
 - Physical on die
 - In path (reconvergent fanout)
 - Makes result conservative
 - Gives upper bound
 - Can compute lower



Graphics from: Noel Menezes (top) and Nikil Mehta (bottom)

Max of Gaussians with Correlation



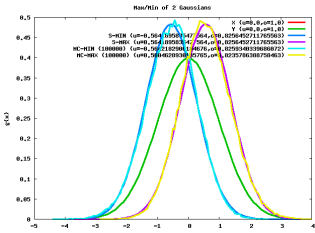
- Max of identical Gaussians

MAX of Two Identical Gaussians

- Given two identical Gaussians A and B with μ and σ
- Plug into equations
- $E[\text{MAX}(A,B)] = \mu + \sigma/(\pi)^{1/2}$
- $\text{VAR}[\text{MAX}(A,B)] = \sigma^2 - \sigma/\pi$

[Source: Nikil Mehta]

Extreme of correlated: is just the input Gaussian



SSTA vs. Monte Carlo Verification Time

TABLE II
MONTE CARLO VERSUS EinsStat COMPARISON

Test case	Gates	EinsStat CPU	Monte Carlo		
			Samples	Sequential CPU dd:hh:mm:ss	Parallel CPU dd:hh:mm:ss
1	18	1 sec.	100000	5:57	N/A
2	3042	2 sec.	100000	2:01:15:10	2:46:55
3	11937	7 sec.	10000	0:20:33:40	51:05
4	70216	59 sec.	10000	N/A	4:36:12

Source: IBM, TRCAD 2006

Using SSTA in FPGA CAD

[Slide composed by Nikil Mehta]

- Le Hei
 - FPGA2007
 - SSTA Synthesis, Place, Route
- Kia
 - FPGA2007
 - Route with SSTA

Process variation settings (1σ)						
global	5.0%	10.0%	15.0%	20.0%	25.0%	30.0%
spatial	5.0%	10.0%	15.0%	20.0%	25.0%	30.0%
local	5.0%	0.0%	0.0%	12.0%	15.0%	18.0%
deterministic flow						
Tmean (ns)	41.7	42.9	44.4	46.2	48.2	50.2
Tsigmas (ns)	1.8	4.4	5.0	6.4	7.8	9.2
stochastic flow						
Tmean (ns)	30.3	31.5	33.0	34.8	36.7	38.6
Tsigmas (ns)	(-6.5%)	(-6.2%)	(-5.8%)	(-5.5%)	(-5.3%)	(-5.1%)
Tsigmas (ns)	1.8	3.1	4.6	5.9	7.2	8.5
	(-6.6%)	(-7.5%)	(-8.1%)	(-8.2%)	(-8.1%)	(-8.0%)

Table 6: Comparison of mean delay and standard deviation between deterministic and stochastic flows under various process variation assumptions (based on the geometric mean of 20 MCNC designs).

Circuit	Delay Impr. (%)
exp	6.58
alu4	1.50
misex3	5.76
apex2	3.24
apex4	2.57
pdic	4.74
seq	4.37
des	3.73
spla	4.82
ex1010	1.83
frisc	2.84
elliptic	0.17
bigkey	0.35
c298	7.10
tseng	5.93
diffeq	4.16
dsip	7.37
s38417	7.56
s38584.1	5.43
clma	-1.17
Mean	3.95

Impact of SSTA in High-Level Synthesis

Design (#ops)	#ALU, #MUL	P_{α} (ns)	Latency(cycles)		Reduction	Run time(s)
			LS[15]	HLS-tv(Y)		
DIFF (18)	3, 3	3.5	32	28 (94.5%)	12.5%	928
		4.0	29	24 (90.7%)	17.2%	930
		4.5	26	22 (93.2%)	15.4%	637
LATT (22)	3, 2	3.5	47	36 (94.3%)	23.4%	2122
		4.0	42	32 (94.3%)	23.8%	3325
		4.5	37	30 (90.2%)	18.9%	1207
AR (28)	2, 3	3.5	57	45 (93.9%)	21.1%	1241
		4.0	51	40 (93.9%)	21.6%	1534
		4.5	45	36 (90.8%)	20.0%	680
EWF (34)	2, 3	3.5	46	37 (93.6%)	19.6%	157
		4.0	42	34 (93.6%)	19.0%	367
		4.5	38	33 (91.5%)	13.2%	113
avg.				-(92.9%)	18.8%	

- Scheduling and provisioning
– ALU/MUL $\sigma=5\%$ t_{nominal}

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[Jung&Kim ICCAD2007]

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Summary

- Nanoscale fabrication is a statistical process
- Delays are PDFs
- Assuming each device is worst-case delay is too pessimistic
 - Wrong prediction about timing
 - Leads optimization in wrong direction
- Reformulate timing analysis as statistical calculation
- Estimate the PDF of circuit delays
- Use this to drive optimizations

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Big Ideas:

- Coping with uncertainty
- Statistical Reasoning and Calculation

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Admin

- Reading for Monday on blackboard
- Milestone Mondays

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